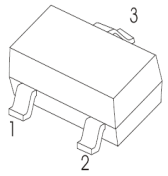
MMBTA64 TRANSISTOR (PNP)

SOT－23



1. BASE
2. EMITTER
3. COLLECTOR

FEATURES

- For Applications Requiring High Current Gain

MARKING:2V

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-10	V
I_C	Collector Current	-800	mA
P_C	Collector Power Dissipation	300	mW
$R_{\Theta JA}$	Thermal Resistance From Junction To Ambient	416	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55～+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-10			V
Collector cut-off current	I_{CBO}	V_{CB}=-30V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-10V, I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$ *	V_{CE}=-5V, I_C=-10mA	10			K
	$h_{FE(2)}$ *	V_{CE}=-5V, I_C=-100mA	20			K
Collector-emitter saturation voltage	$V_{CE(sat)}$ *	I_C=-100mA, I_B=-0.1mA			-1.5	V
Base-emitter voltage	V_{BE}*	V_{CE}=-5V, I_C=-100mA			-2	V
Transition frequency	f_T	V_{CE}=-5V,I_C=-10mA, f=100MHz	125			MHz

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.